ETCHING METHOD AND PLASMA PROCESSING APPARATUS

ABSTRACT

An etching method and a plasma processing apparatus form a recess with an intended shape. The etching method includes (a) providing a substrate including a silicon-containing film and a mask on the silicon-containing film; (b) etching the silicon-containing film with a first plasma to form a recess, the first plasma generated from a first process gas; (c) supplying a second plasma to the substrate, the second plasma generated from a second process gas comprising tungsten; and (d) etching the recess with a third plasma generated from a third process gas.

[Figure.3]